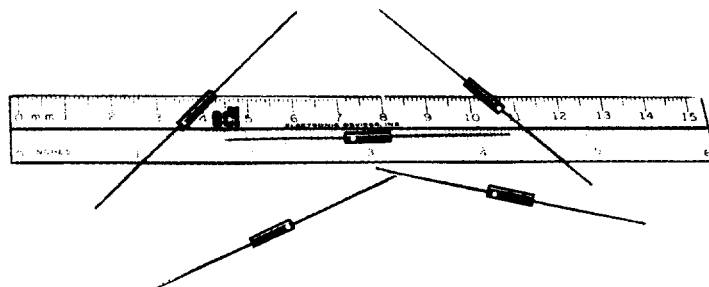


FAST RECOVERY HIGH VOLTAGE 25 mA MINIATURE SILICON RECTIFIERS

- SMALL SIZE MOLDED PACKAGE
- PRV 3,000 TO 12,000 VOLTS
- 1.0 INCH MIN. LEADS
- LOW LEAKAGE



EDI Type	PRV Volts
DL 300	3,000
DL 500	5,000
DL 800	8,000
DL 1000	10,000
DL 1200	12,000

ELECTRICAL CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Average Rectified Forward Current @ 50°C , I_O	25 mA
Max. Peak Surge Current, I_{FSM} (8.3ms)	3 Amp
Max. Reverse Recovery t_r (Fig. 4)	150 nanosec
Max. Forward Voltage Drop @ 25mA, V_F	26 Volts
Max. DC Reverse Current @ PRV and 25°C , I_R	$1\mu\text{A}$
Max. DC Reverse Current @ PRV and 100°C , I_R	$25\mu\text{A}$
Ambient Operating Temperature Range, T_A	-55°C to $+125^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55°C to $+150^\circ\text{C}$

NOTES:

1. It is recommended that a proper heat sink be used on the terminals of this device between the body and the soldering point to prevent damage from excess heat.
2. If operated over 10,000 v/inch in length, devices should be immersed in oil or re-encapsulated.

EDI reserves the right to change these specifications at any time without notice.

FIG. 1

OUTPUT CURRENT vs AMBIENT TEMPERATURE

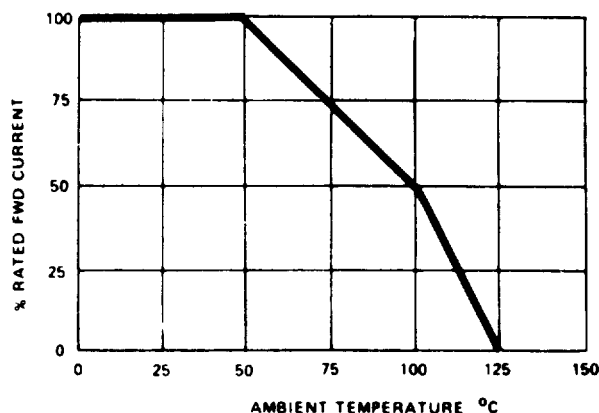


FIG. 2

NON - REPETITIVE SURGE CURRENT

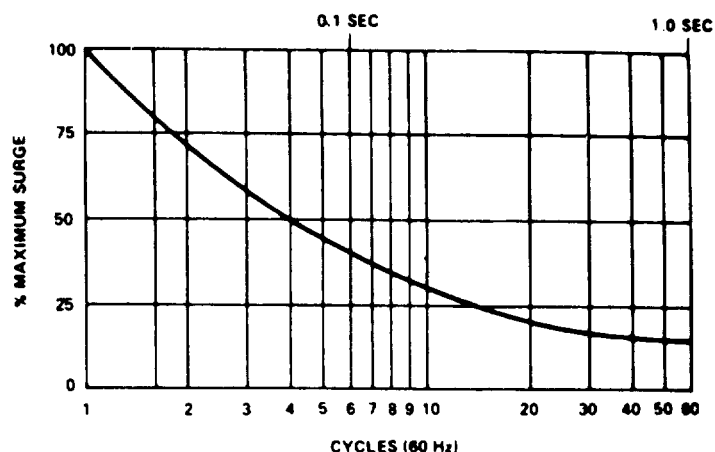


FIG. 3
MECHANICAL

LEAD - SOLDER DIPPED COPPER
MARKING: CATHODE BAND
AND DEVICE TYPE

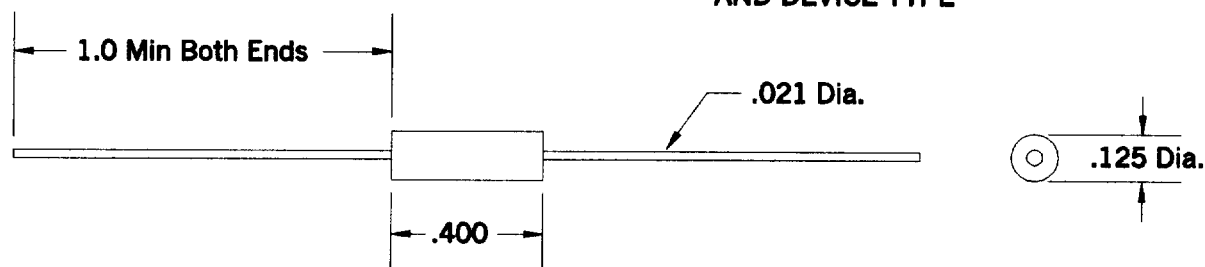
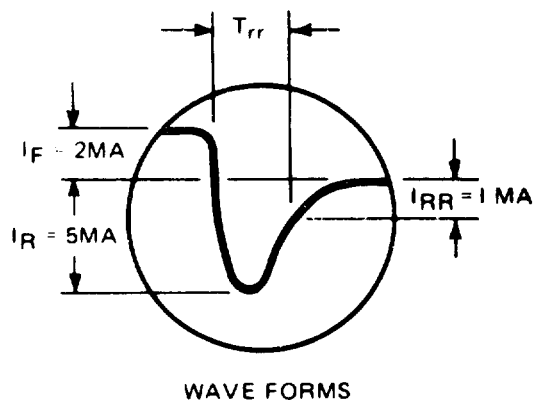


FIG. 4

REVERSE RECOVERY TEST METHOD

RECOVERY WAVE FORM



RECOVERY TEST CIRCUIT

